



**10NM70-U2**

Preliminary

**Power MOSFET**

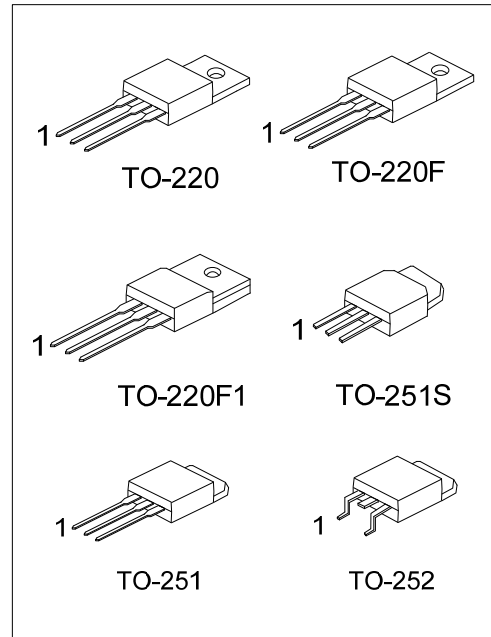
**10A, 700V N-CHANNEL  
SUPER-JUNCTION MOSFET**

■ DESCRIPTION

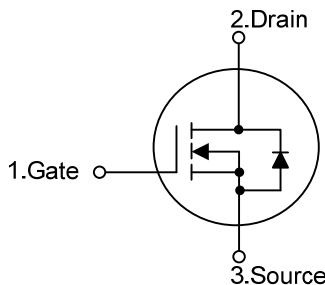
The **UTC 10NM70-U2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

- \*  $R_{DS(ON)} < 0.69\Omega @ V_{GS}=10V, I_D=5.0A$
- \* By using Super Junction Structure
- \* Fast Switching
- \* With 100% Avalanche Tested



■ SYMBOL



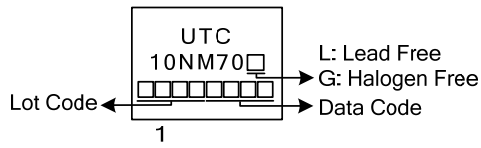
■ ORDERING INFORMATION

| Ordering Number |               | Package  | Pin Assignment |   |   | Packing   |
|-----------------|---------------|----------|----------------|---|---|-----------|
| Lead Free       | Halogen Free  |          | 1              | 2 | 3 |           |
| 10NM70L-TA3-T   | 10NM70G-TA3-T | TO-220   | G              | D | S | Tube      |
| 10NM70L-TF3-T   | 10NM70G-TF3-T | TO-220F  | G              | D | S | Tube      |
| 10NM70L-TF1-T   | 10NM70G-TF1-T | TO-220F1 | G              | D | S | Tube      |
| 10NM70L-TM3-T   | 10NM70G-TM3-T | TO-251   | G              | D | S | Tube      |
| 10NM70L-TMS-T   | 10NM70G-TMS-T | TO-251S  | G              | D | S | Tube      |
| 10NM70L-TN3-R   | 10NM70G-TN3-R | TO-252   | G              | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

|  |   |
|--|---|
| <p>10NM70G-TF1-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p> | <p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TM3: TO-251, TMS: TO-251S, TN3: TO-252</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p> |
|--|---|

### MARKING



FLYING 汎翔國際有限公司  
www.flying1688.com

■ ABSOLUTE MAXIMUM RATINGS ( $T_c = 25^\circ\text{C}$ , unless otherwise specified)

| PARAMETER                          |                        | SYMBOL    | RATINGS    | UNIT             |
|------------------------------------|------------------------|-----------|------------|------------------|
| Drain-Source Voltage               |                        | $V_{DSS}$ | 700        | V                |
| Gate-Source Voltage                |                        | $V_{GSS}$ | $\pm 30$   | V                |
| Drain Current                      | Continuous             | $I_D$     | 10         | A                |
|                                    | Pulsed (Note 2)        | $I_{DM}$  | 40         | A                |
| Avalanche Current (Note 2)         |                        | $I_{AR}$  | 2.4        | A                |
| Avalanche Energy                   | Single Pulsed (Note 3) | $E_{AS}$  | 208        | mJ               |
| Peak Diode Recovery dv/dt (Note 4) |                        | dv/dt     | 5.2        | V/ns             |
| Power Dissipation                  | TO-220                 | $P_D$     | 150        | W                |
|                                    | TO-220F/TO-220F1       |           | 50         | W                |
|                                    | TO-251/TO-251S         |           | 75         | W                |
|                                    | TO-252                 |           |            |                  |
| Junction Temperature               |                        | $T_J$     | +150       | $^\circ\text{C}$ |
| Storage Temperature Range          |                        | $T_{STG}$ | -55 ~ +150 | $^\circ\text{C}$ |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3.  $L=79\text{mH}$ ,  $I_{AS}=2.3\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$

4.  $I_{SD}\leq 10\text{A}$ ,  $di/dt\leq 200\text{A}/\mu\text{s}$ ,  $V_{DD}\leq BV_{DSS}$ , Starting  $T_J=25^\circ\text{C}$

■ THERMAL DATA

| PARAMETER           |                            | SYMBOL        | RATING           | UNIT                      |               |      |                           |
|---------------------|----------------------------|---------------|------------------|---------------------------|---------------|------|---------------------------|
| Junction to Ambient | TO-220/TO-220F<br>TO-220F1 | $\theta_{JA}$ | 62.5             | $^\circ\text{C}/\text{W}$ |               |      |                           |
|                     | TO-251/TO-251S<br>TO-252   |               | 110              |                           |               |      |                           |
|                     | Junction to Case           |               | TO-220           |                           | $\theta_{JC}$ | 0.83 | $^\circ\text{C}/\text{W}$ |
|                     |                            |               | TO-220F/TO-220F1 |                           |               | 2.5  |                           |
| TO-251/TO-251S      |                            | 1.67          |                  |                           |               |      |                           |
| TO-252              |                            |               |                  |                           |               |      |                           |

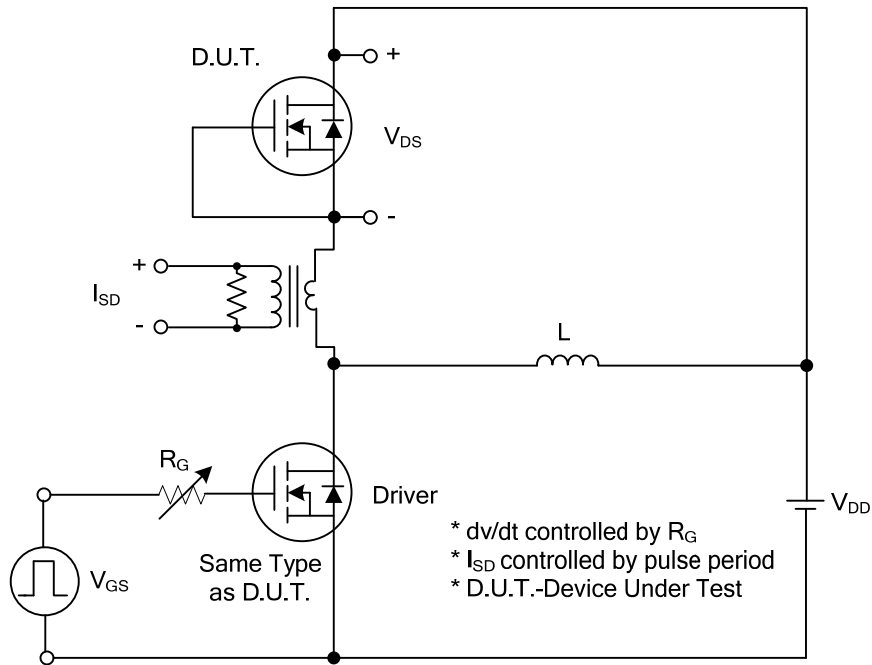
■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

| PARAMETER  | SYMBOL              | TEST CONDITIONS   | MIN | TYP  | MAX  | UNIT |
|--|---------------------|---|-----|------|------|------|
| <b>OFF CHARACTERISTICS</b>                             |                     |   |     |      |      |      |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V, I <sub>D</sub> =250μA  | 700 |      |      | V    |
| Drain-Source Leakage Current                           | I <sub>DSS</sub>    | V <sub>DS</sub> =700V, V <sub>GS</sub> =0V  |     |      | 10   | μA   |
| Gate-Source Leakage Current                            | Forward             | V <sub>DS</sub> =0V, V <sub>GS</sub> =30V   |     |      | 100  | nA   |
|  | Reverse             |   |     |      |      |      |
| <b>ON CHARACTERISTICS</b>                              |                     |   |     |      |      |      |
| Gate Threshold Voltage                                 | V <sub>GS(TH)</sub> | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA  | 2.5 |      | 4.5  | V    |
| Drain-Source On-State Resistance                       | R <sub>DS(ON)</sub> | V <sub>GS</sub> =10V, I <sub>D</sub> =5.0A  |     | 0.53 | 0.69 | Ω    |
| <b>DYNAMIC PARAMETERS</b>                              |                     |   |     |      |      |      |
| Input Capacitance                                      | C <sub>ISS</sub>    | V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz   |     | 540  |      | pF   |
| Output Capacitance                                     | C <sub>OSS</sub>    |   |     | 382  |      | pF   |
| Reverse Transfer Capacitance                           | C <sub>RSS</sub>    |   |     | 33   |      | pF   |
| <b>SWITCHING PARAMETERS</b>                            |                     |   |     |      |      |      |
| Total Gate Charge (Note 1)                             | Q <sub>G</sub>      | V <sub>DS</sub> =50V, V <sub>GS</sub> =10V, I <sub>D</sub> =1.3A, I <sub>G</sub> =100μA (Note 1, 2) |     | 61.6 |      | nC   |
| Gate to Source Charge                                  | Q <sub>GS</sub>     |   |     | 3.8  |      | nC   |
| Gate to Drain Charge                                   | Q <sub>GD</sub>     |   |     | 15   |      | nC   |
| Turn-ON Delay Time (Note 1)                            | t <sub>D(ON)</sub>  | V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A, R <sub>G</sub> =25Ω (Note 1, 2)   |     | 40   |      | ns   |
| Rise Time  | t <sub>R</sub>      |   |     | 81   |      | ns   |
| Turn-OFF Delay Time                                    | t <sub>D(OFF)</sub> |   |     | 196  |      | ns   |
| Fall-Time  | t <sub>F</sub>      |   |     | 91   |      | ns   |
| <b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b> |                     |   |     |      |      |      |
| Maximum Body-Diode Continuous Current                  | I <sub>S</sub>      |   |     |      | 10   | A    |
| Maximum Body-Diode Pulsed Current                      | I <sub>SM</sub>     |   |     |      | 40   | A    |
| Drain-Source Diode Forward Voltage (Note 1)            | V <sub>SD</sub>     | I <sub>S</sub> =10A, V <sub>GS</sub> =0V  |     |      | 1.4  | V    |
| Body Diode Reverse Recovery Time (Note 1)              | t <sub>rr</sub>     | I <sub>S</sub> =10A, V <sub>GS</sub> =0V, dI <sub>F</sub> /dt=100A/μs                               |     | 118  |      | ns   |
| Body Diode Reverse Recovery Charge                     | Q <sub>rr</sub>     |   |     | 0.29 |      | μC   |

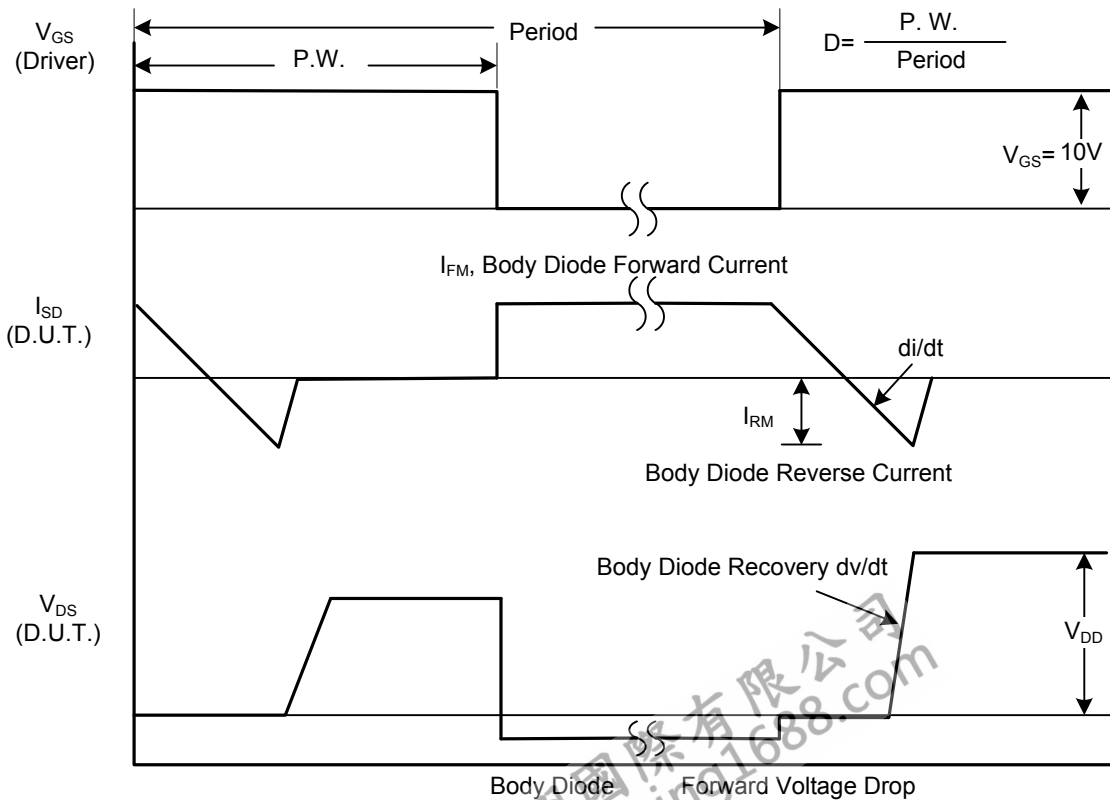
Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

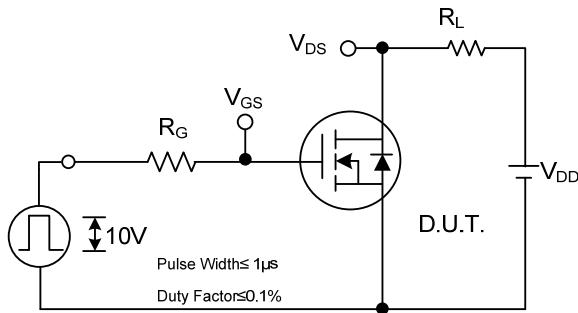


Peak Diode Recovery  $dv/dt$  Test Circuit

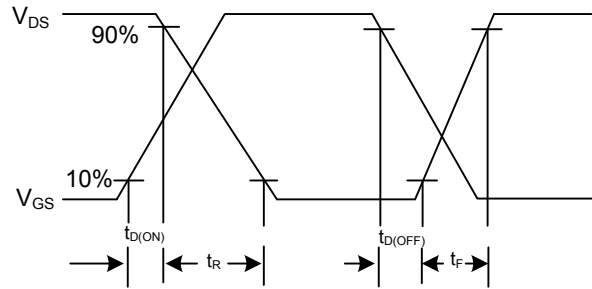


Peak Diode Recovery  $dv/dt$  Waveforms

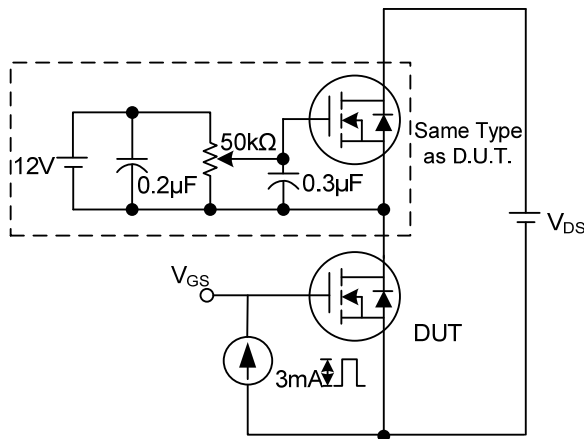
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



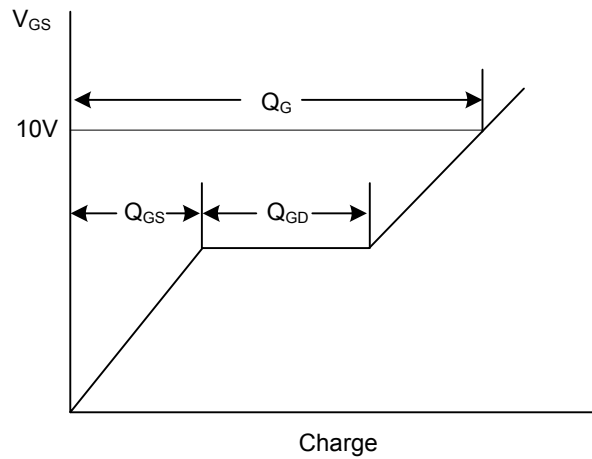
Switching Test Circuit



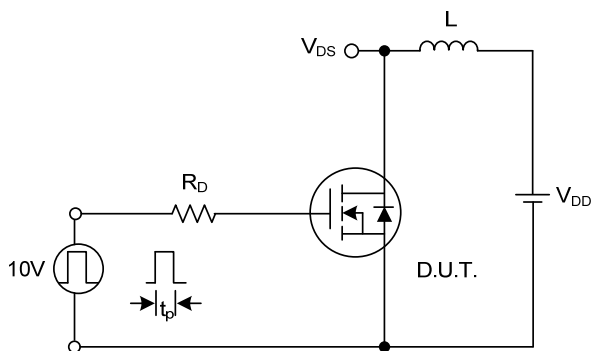
Switching Waveforms



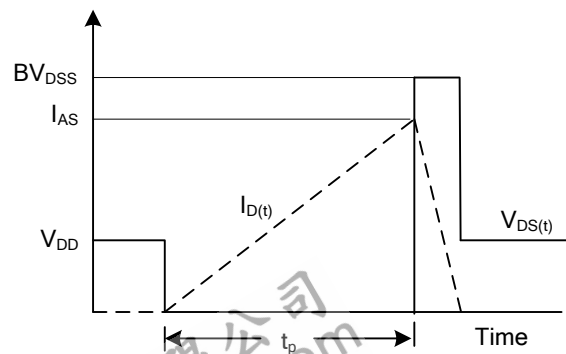
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.